

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	MOS and (gate adj oxide) and ammonia and hydrogen and peroxide and (second adj thickness) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:51
L3	0	MOS and (gate adj oxide) and (ammonia-hydrogen) and peroxide and (second adj thickness) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:51
L4	0	MOS and (gate adj oxide) and (ammonia with peroxide) and (second adj thickness) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:52
L5	1	MOS and (gate adj oxide) and SC1 and (second adj thickness) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:53
L6	0	MOS and (gate adj oxide) and (ammonia with clean) and (second adj thickness) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:53
L7	9	MOS and (gate adj oxide) and (ammonia with clean) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:33
L8	0	MOS and (gate adj oxide) and (ammonia with clean) and (nitride with ammonia) and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:33
L9	79	MOS and (gate adj oxide) and (nitride with ammonia) and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:34

L10	2	MOS and (gate adj oxide) and (nitride with ammonia) and (silicon adj oxide) and oxynitride and (second adj thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:34
S1	564	(438/758).CCLS.	USPAT	OR	OFF	2004/12/02 15:40
S2	1587	semiconductor and (silicon adj oxide) and film and ammonia and (hydrogen adj peroxide) and nitrid\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 15:42
S3	944	semiconductor and (silicon adj oxide) and film and ammonia and (hydrogen adj peroxide) and nitrid\$	USPAT	OR	ON	2004/12/02 15:42
S4	84	semiconductor and (silicon adj oxide) and film and ammonia and (hydrogen adj peroxide) and nitriding	USPAT	OR	ON	2004/12/02 15:42
S5	63	semiconductor and (silicon adj oxide) and ammonia and (hydrogen adj peroxide) and (nitriding with film)	USPAT	OR	ON	2004/12/02 15:43
S6	21	semiconductor and (silicon adj oxide) and (ammonia adj gas) and (hydrogen adj peroxide) and (nitriding with film)	USPAT	OR	ON	2004/12/02 16:57
S7	3	("6032801") or ("5579686") or ("5441154") PN	USPAT	OR	OFF	2005/03/30 14:40
S8	1127	(438/622).CCLS.	USPAT	OR	OFF	2004/12/02 16:57
S9	774	(438/618).CCLS.	USPAT	OR	OFF	2004/12/02 16:58
S10	1063	(438/624).CCLS.	USPAT	OR	OFF	2004/12/02 16:58
S11	1	("6815330") PN	USPAT	OR	OFF	2005/03/30 15:18
S12	37	MOS and (gate adj oxide) and ammonia and (second adj thickness) and nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 15:19
S13	6	MOS and (gate adj oxide) and ammonia and (second adj thickness) and nitride and (silicon adj oxide) and oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:46